

## 4 MHz, Low-Input Bias Current Op Amps

### Features

- **Low-Input Bias Current**
  - 150 pA (typical,  $T_A = +125^\circ\text{C}$ )
- **Low Quiescent Current**
  - 240  $\mu\text{A}$ /amplifier (typical)
- **Low-Input Offset Voltage**
  - $\pm 1.5$  mV (maximum)
- Supply Voltage Range: 2.2V to 5.5V
- Rail-to-Rail Input/Output
- Gain Bandwidth Product: 4 MHz (typical)
- Slew Rate: 2.7 V/ $\mu\text{s}$  (typical)
- Unity Gain Stable
- No Phase Reversal
- Small Packages
  - Singles in SC70-5, SOT-23-5
- Extended Temperature Range
  - $-40^\circ\text{C}$  to  $+125^\circ\text{C}$

### Applications

- Photodiode Amplifier
- pH Electrode Amplifier
- Low Leakage Amplifier
- Piezoelectric Transducer Amplifier
- Active Analog Filter
- Battery-Powered Signal Conditioning

### Design Aids

- SPICE Macro Models
- FilterLab<sup>®</sup> Software
- MAPS (Microchip Advanced Part Selector)
- Analog Demonstration and Evaluation Boards
- Application Notes

### Description

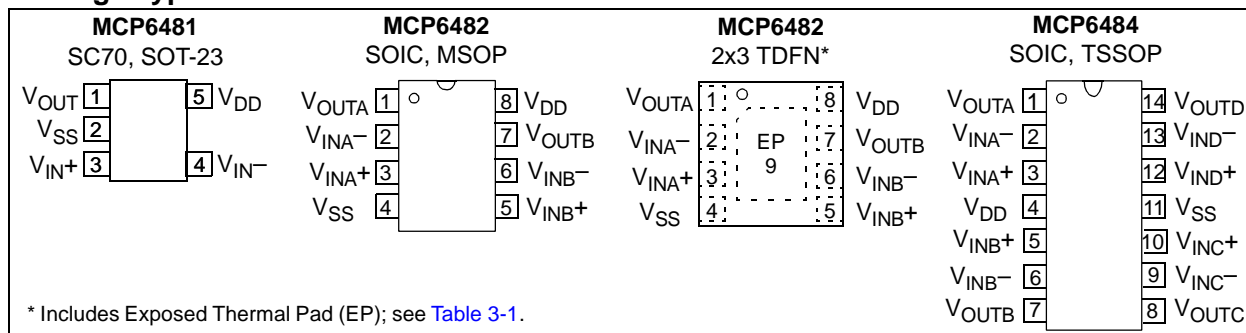
The Microchip MCP6481/2/4 family of operational amplifiers (op amps) has low-input bias current (150 pA, typical at  $125^\circ\text{C}$ ) and rail-to-rail input and output operation. This family is unity gain stable and has a gain bandwidth product of 4 MHz (typical). These devices operate with a single-supply voltage as low as 2.2V, while only drawing 240  $\mu\text{A}$ /amplifier (typical) of quiescent current. These features make the family of op amps well suited for photodiode amplifier, pH electrode amplifier, low leakage amplifier, and battery-powered signal conditioning applications, etc.

The MCP6481/2/4 family is offered in single (MCP6481), dual (MCP6482), quad (MCP6484) packages. All devices are designed using an advanced CMOS process and fully specified in extended temperature range from  $-40^\circ\text{C}$  to  $+125^\circ\text{C}$ .

### Related Parts

- MCP6471/2/4: 2 MHz, Low-Input Bias Current Op Amps
- MCP6491/2/4: 7.5 MHz, Low-Input Bias Current Op Amps

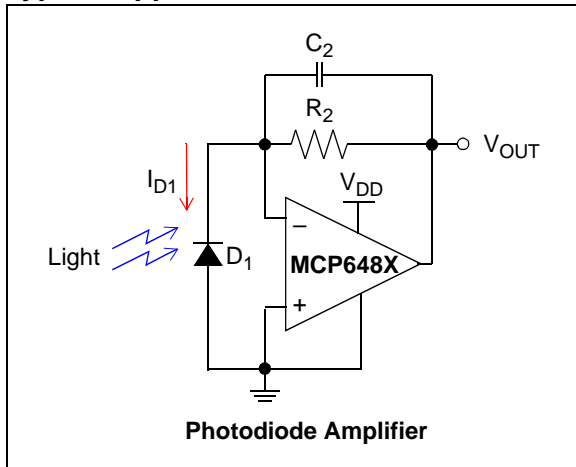
### Package Types



# MCP6481/2/4

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## Typical Application



## 1.0 ELECTRICAL CHARACTERISTICS

### 1.1 Absolute Maximum Ratings †

$V_{DD} - V_{SS}$ .....	6.5V
Current at Input Pins .....	±2 mA
Analog Inputs ( $V_{IN+}$ , $V_{IN-}$ )†† .....	$V_{SS} - 1.0V$ to $V_{DD} + 1.0V$
All Other Inputs and Outputs .....	$V_{SS} - 0.3V$ to $V_{DD} + 0.3V$
Difference Input Voltage.....	$V_{DD} - V_{SS}$
Output Short-Circuit Current .....	continuous
Current at Output and Supply Pins .....	±55 mA
Storage Temperature .....	-65°C to +150°C
Maximum Junction Temperature ( $T_J$ ).....	+150°C
ESD protection on all pins (HBM) .....	≥ 4 kV

**Note 1:** See [Section 4.1.2, Input Voltage Limits](#).

† **Notice:** Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

### 1.2 Specifications

**TABLE 1-1: DC ELECTRICAL SPECIFICATIONS**

Electrical Characteristics: Unless otherwise indicated, $V_{DD} = +2.2V$ to $+5.5V$ , $V_{SS} = GND$ , $T_A = +25^\circ C$ , $V_{CM} = V_{DD}/2$ , $V_{OUT} \approx V_{DD}/2$ , $V_L = V_{DD}/2$ and $R_L = 10\text{ k}\Omega$ to $V_L$ . (Refer to <a href="#">Figure 1-1</a> ).						
Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
<b>Input Offset</b>						
Input Offset Voltage	$V_{OS}$	-1.5	—	+1.5	mV	$V_{DD} = 3.0V$ , $V_{CM} = V_{DD}/4$
Input Offset Drift with Temperature	$\Delta V_{OS}/\Delta T_A$	—	±2.5	—	$\mu V/^\circ C$	$T_A = -40^\circ C$ to $+125^\circ C$
Power Supply Rejection Ratio	PSRR	75	91	—	dB	$V_{CM} = V_{DD}/4$
<b>Input Bias Current and Impedance</b>						
Input Bias Current	$I_B$	—	±1	—	pA	
		—	8	—	pA	$T_A = +85^\circ C$
		—	150	350	pA	$T_A = +125^\circ C$
Input Offset Current	$I_{OS}$	—	±0.1	—	pA	
Common Mode Input Impedance	$Z_{CM}$	—	$10^{13}  6$	—	$\Omega  pF$	
Differential Input Impedance	$Z_{DIFF}$	—	$10^{13}  6$	—	$\Omega  pF$	
<b>Common Mode</b>						
Common Mode Input Voltage Range	$V_{CMR}$	$V_{SS} - 0.3$	—	$V_{DD} + 0.3$	V	
Common Mode Rejection Ratio	CMRR	65	87	—	dB	$V_{CM} = -0.3V$ to $2.5V$ , $V_{DD} = 2.2V$
		70	89	—	dB	$V_{CM} = -0.3V$ to $5.8V$ , $V_{DD} = 5.5V$
<b>Open-Loop Gain</b>						
DC Open-Loop Gain (Large Signal)	$A_{OL}$	95	115	—	dB	$0.2V < V_{OUT} < (V_{DD} - 0.2V)$ $V_{DD} = 5.5V$ , $V_{CM} = V_{SS}$

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**TABLE 1-1: DC ELECTRICAL SPECIFICATIONS (CONTINUED)**

**Electrical Characteristics:** Unless otherwise indicated,  $V_{DD} = +2.2V$  to  $+5.5V$ ,  $V_{SS} = GND$ ,  $T_A = +25^\circ C$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$  and  $R_L = 10\text{ k}\Omega$  to  $V_L$ . (Refer to [Figure 1-1](#)).

Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
<b>Output</b>						
High-Level Output Voltage	$V_{OH}$	2.180	2.196	—	V	$V_{DD} = 2.2V$ 0.5V input overdrive
		5.480	5.493	—	V	$V_{DD} = 5.5V$ 0.5V input overdrive
Low-Level Output Voltage	$V_{OL}$	—	0.004	0.020	V	$V_{DD} = 2.2V$ 0.5 V input overdrive
		—	0.007	0.020	V	$V_{DD} = 5.5V$ 0.5 V input overdrive
Output Short-Circuit Current	$I_{SC}$	—	$\pm 12$	—	mA	$V_{DD} = 2.2V$
		—	$\pm 36$	—	mA	$V_{DD} = 5.5V$
<b>Power Supply</b>						
Supply Voltage	$V_{DD}$	2.2	—	5.5	V	
Quiescent Current per Amplifier	$I_Q$	100	240	400	$\mu A$	$I_O = 0$ , $V_{CM} = V_{DD}/4$

**TABLE 1-2: AC ELECTRICAL SPECIFICATIONS**

**Electrical Characteristics:** Unless otherwise indicated,  $T_A = +25^\circ C$ ,  $V_{DD} = +2.2V$  to  $+5.5V$ ,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 20\text{ pF}$ . (Refer to [Figure 1-1](#)).

Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
<b>AC Response</b>						
Gain Bandwidth Product	GBWP	—	4	—	MHz	
Phase Margin	PM	—	60	—	$^\circ$	$G = +1V/V$
Slew Rate	SR	—	2.7	—	V/ $\mu s$	
<b>Noise</b>						
Input Noise Voltage	$E_{ni}$	—	7	—	$\mu V_{p-p}$	$f = 0.1\text{ Hz to }10\text{ Hz}$
Input Noise Voltage Density	$e_{ni}$	—	23	—	nV/ $\sqrt{Hz}$	$f = 1\text{ kHz}$
		—	18	—	nV/ $\sqrt{Hz}$	$f = 10\text{ kHz}$
Input Noise Current Density	$i_{ni}$	—	0.6	—	fA/ $\sqrt{Hz}$	$f = 1\text{ kHz}$

**TABLE 1-3: TEMPERATURE SPECIFICATIONS**

**Electrical Characteristics:** Unless otherwise indicated,  $V_{DD} = +2.2V$  to  $+5.5V$  and  $V_{SS} = GND$ .

Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
<b>Temperature Ranges</b>						
Operating Temperature Range	$T_A$	-40	—	+125	$^\circ C$	<a href="#">Note 1</a>
Storage Temperature Range	$T_A$	-65	—	+150	$^\circ C$	
<b>Thermal Package Resistances</b>						
Thermal Resistance, 5L-SC-70	$\theta_{JA}$	—	331	—	$^\circ C/W$	
Thermal Resistance, 5L-SOT-23	$\theta_{JA}$	—	256	—	$^\circ C/W$	
Thermal Resistance, 8L-2x3 TDFN	$\theta_{JA}$	—	52.5	—	$^\circ C/W$	
Thermal Resistance, 8L-MSOP	$\theta_{JA}$	—	211	—	$^\circ C/W$	
Thermal Resistance, 8L-SOIC	$\theta_{JA}$	—	149.5	—	$^\circ C/W$	
Thermal Resistance, 14L-SOIC	$\theta_{JA}$	—	95.3	—	$^\circ C/W$	
Thermal Resistance, 14L-TSSOP	$\theta_{JA}$	—	100	—	$^\circ C/W$	

**Note 1:** The internal junction temperature ( $T_J$ ) must not exceed the absolute maximum specification of  $+150^\circ C$ .

## 1.3 Test Circuits

The circuit used for most DC and AC tests is shown in [Figure 1-1](#). This circuit can independently set  $V_{CM}$  and  $V_{OUT}$  (refer to [Equation 1-1](#)). Note that  $V_{CM}$  is not the circuit's common mode voltage  $((V_P + V_M)/2)$ , and that  $V_{OST}$  includes  $V_{OS}$  plus the effects (on the input offset error,  $V_{OST}$ ) of temperature, CMRR, PSRR and  $A_{OL}$ .

### EQUATION 1-1:

$$G_{DM} = R_F/R_G$$

$$V_{CM} = (V_P + V_{DD}/2)/2$$

$$V_{OST} = V_{IN+} - V_{IN-}$$

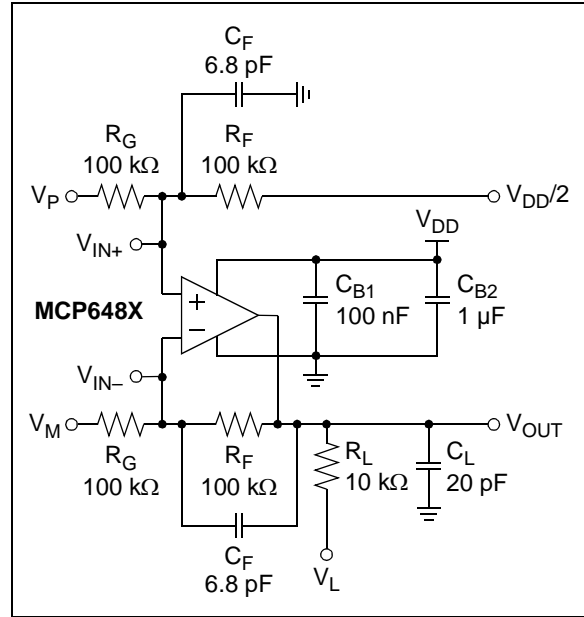
$$V_{OUT} = (V_{DD}/2) + (V_P - V_M) + V_{OST} \cdot (1 + G_{DM})$$

Where:

$$G_{DM} = \text{Differential Mode Gain} \quad (V/V)$$

$$V_{CM} = \text{Op Amp's Common Mode Input Voltage} \quad (V)$$

$$V_{OST} = \text{Op Amp's Total Input Offset Voltage} \quad (mV)$$



**FIGURE 1-1:** AC and DC Test Circuit for Most Specifications.

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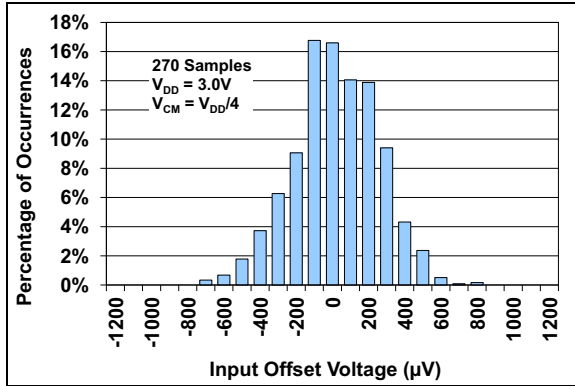
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NOTES:

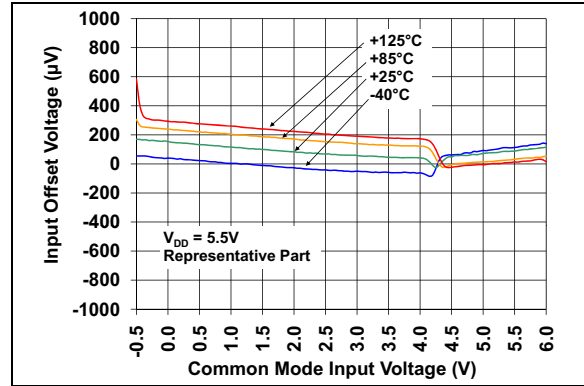
## 2.0 TYPICAL PERFORMANCE CURVES

**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

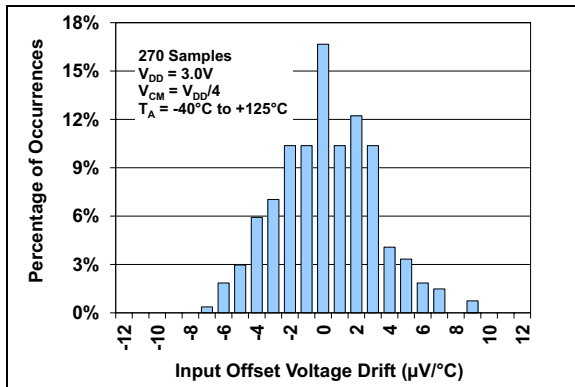
**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = +2.2\text{V}$  to  $+5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 20\text{ pF}$ .



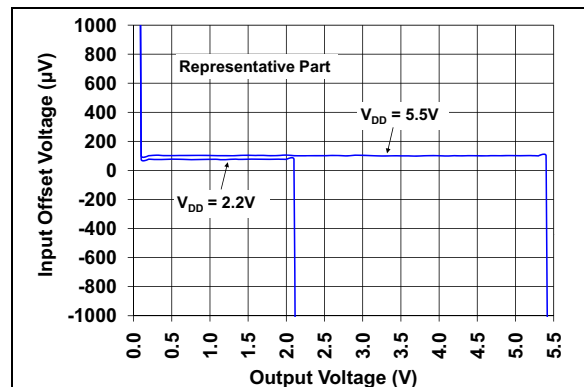
**FIGURE 2-1:** Input Offset Voltage.



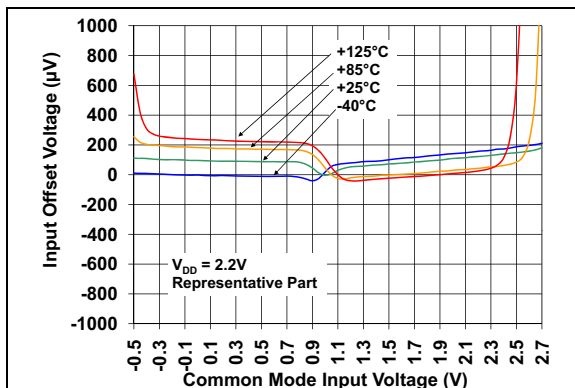
**FIGURE 2-4:** Input Offset Voltage vs. Common Mode Input Voltage.



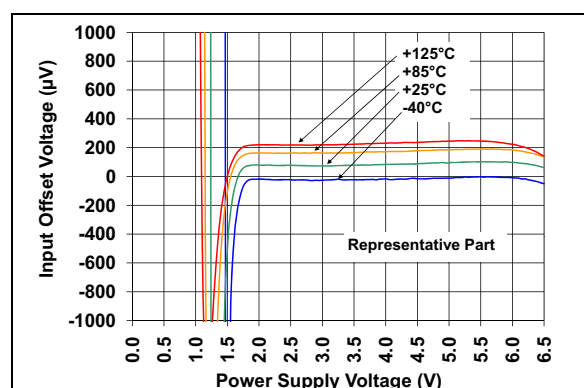
**FIGURE 2-2:** Input Offset Voltage Drift.



**FIGURE 2-5:** Input Offset Voltage vs. Output Voltage.



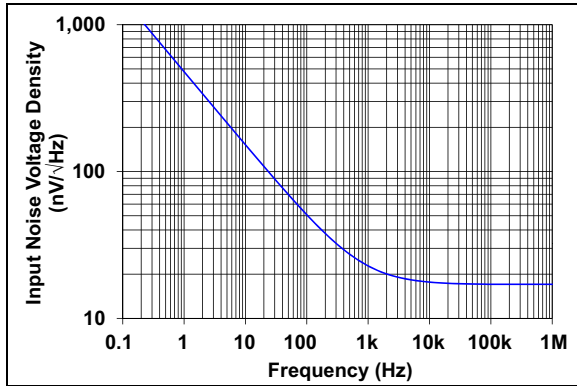
**FIGURE 2-3:** Input Offset Voltage vs. Common Mode Input Voltage.



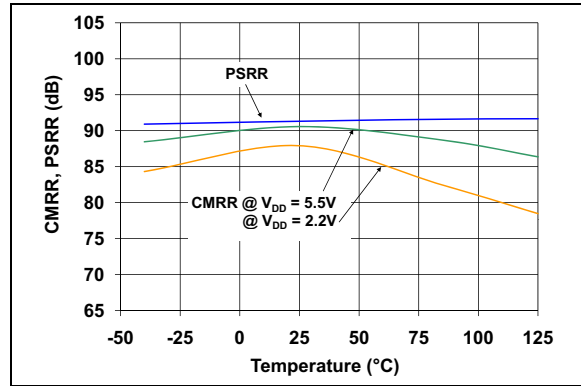
**FIGURE 2-6:** Input Offset Voltage vs. Power Supply Voltage.

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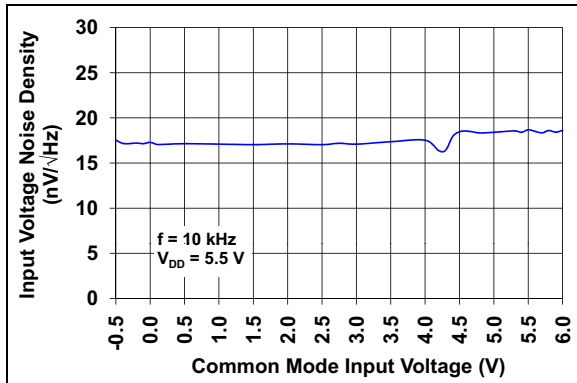
**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = +2.2\text{V}$  to  $+5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 20\text{ pF}$ .



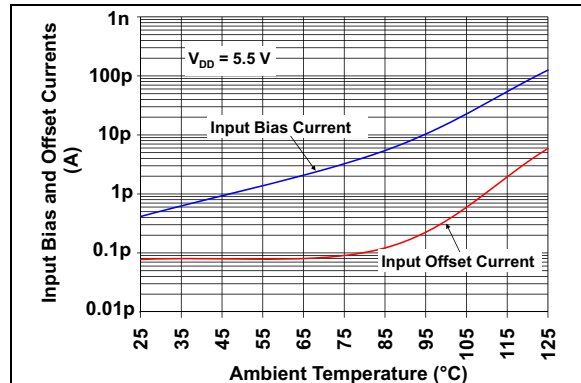
**FIGURE 2-7:** Input Noise Voltage Density vs. Frequency.



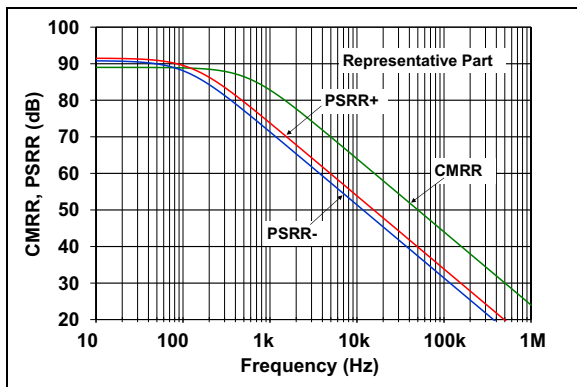
**FIGURE 2-10:** CMRR, PSRR vs. Ambient Temperature.



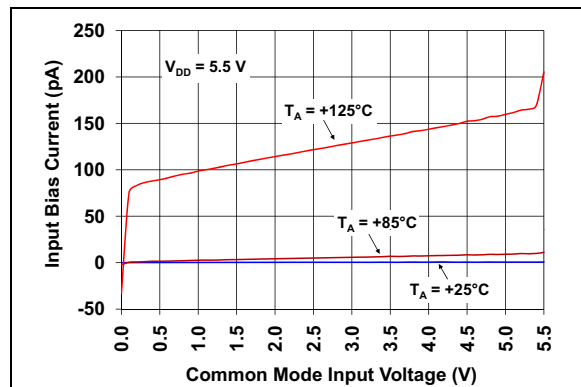
**FIGURE 2-8:** Input Noise Voltage Density vs. Common Mode Input Voltage.



**FIGURE 2-11:** Input Bias, Offset Currents vs. Ambient Temperature.



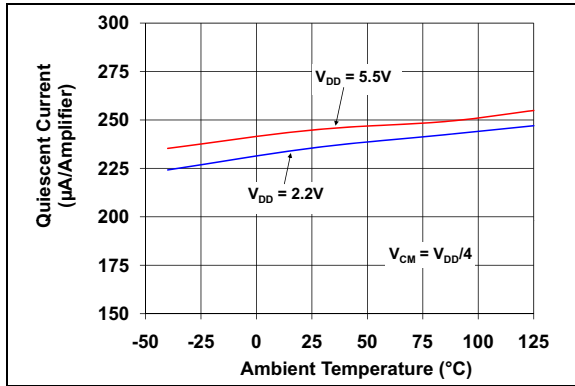
**FIGURE 2-9:** CMRR, PSRR vs. Frequency.



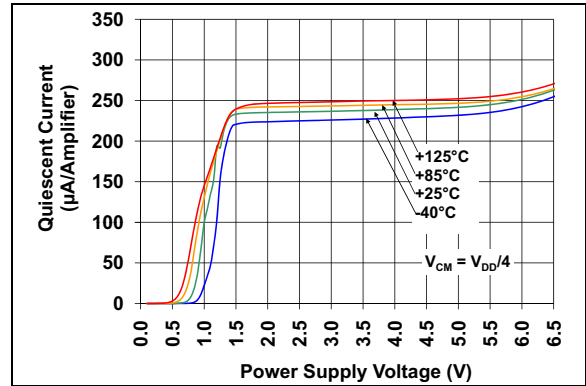
**FIGURE 2-12:** Input Bias Current vs. Common Mode Input Voltage.



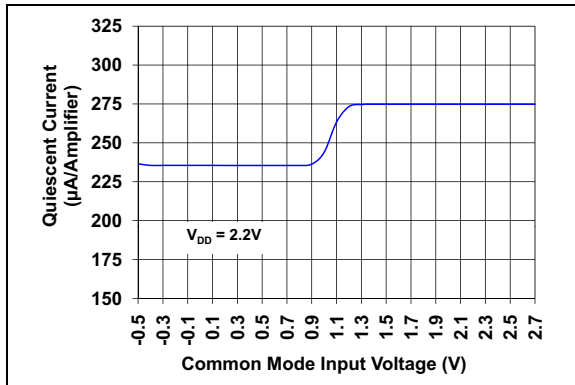
**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = +2.2\text{V}$  to  $+5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 20\text{ pF}$ .



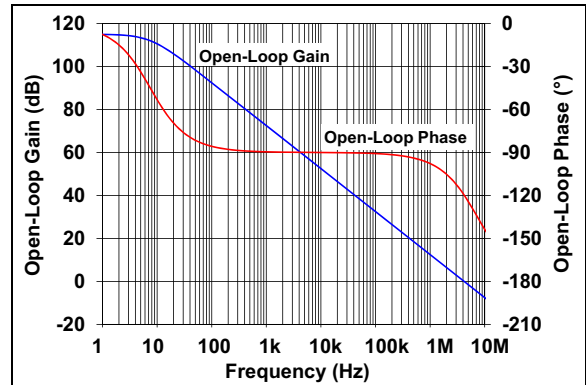
**FIGURE 2-13:** Quiescent Current vs. Ambient Temperature.



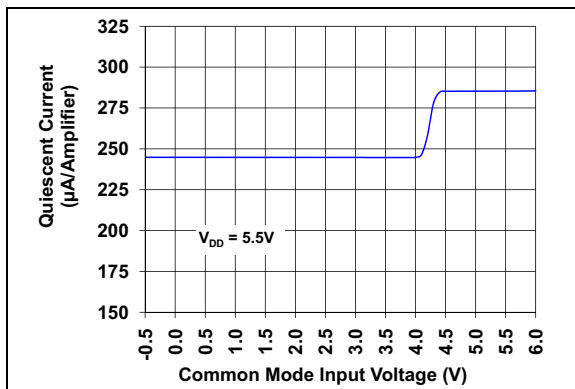
**FIGURE 2-16:** Quiescent Current vs. Power Supply Voltage.



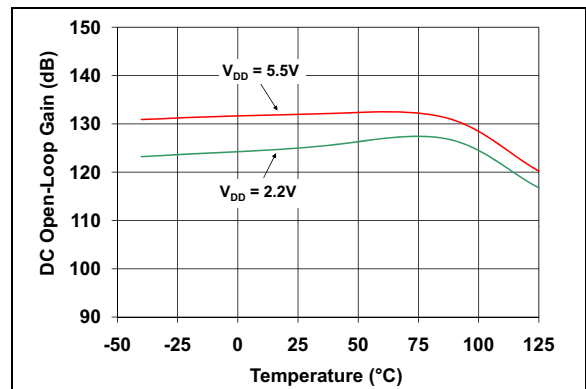
**FIGURE 2-14:** Quiescent Current vs. Common Mode Input Voltage.



**FIGURE 2-17:** Open-Loop Gain, Phase vs. Frequency.



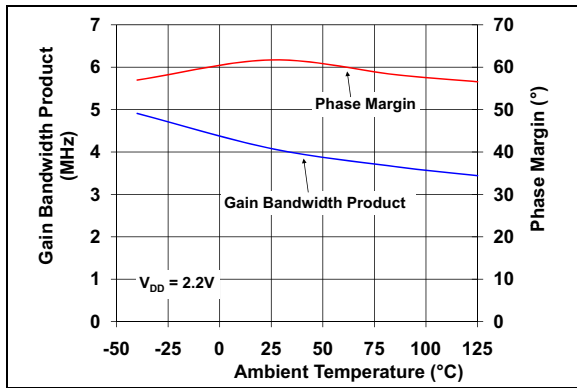
**FIGURE 2-15:** Quiescent Current vs. Common Mode Input Voltage.



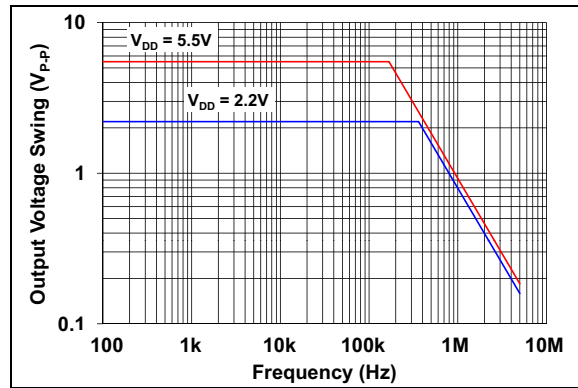
**FIGURE 2-18:** DC Open-Loop Gain vs. Ambient Temperature.

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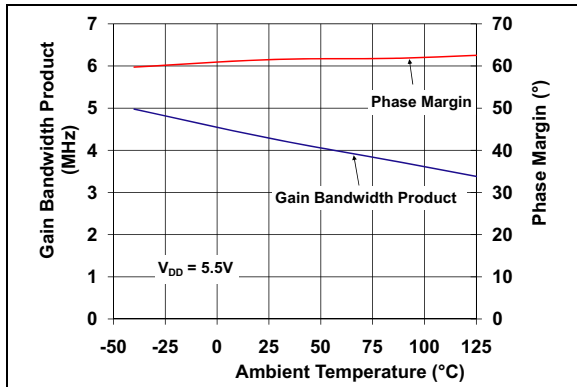
**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = +2.2\text{V}$  to  $+5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 20\text{ pF}$ .



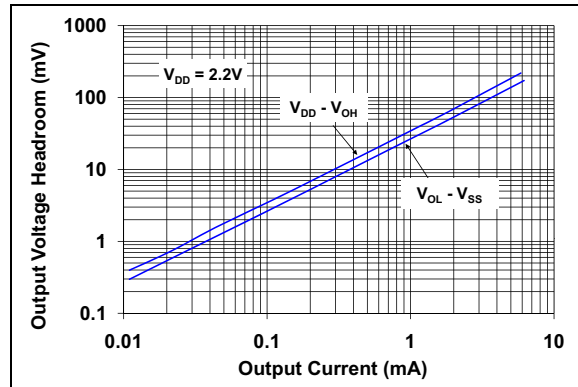
**FIGURE 2-19:** Gain Bandwidth Product, Phase Margin vs. Ambient Temperature.



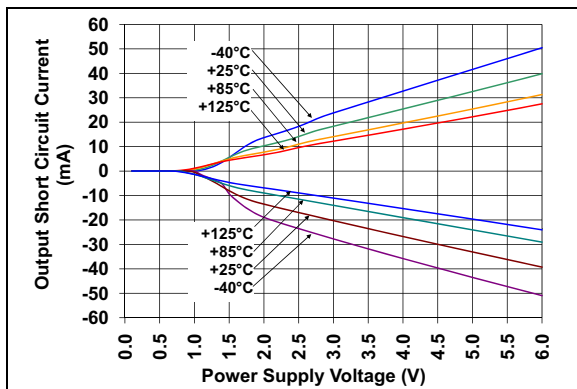
**FIGURE 2-22:** Output Voltage Swing vs. Frequency.



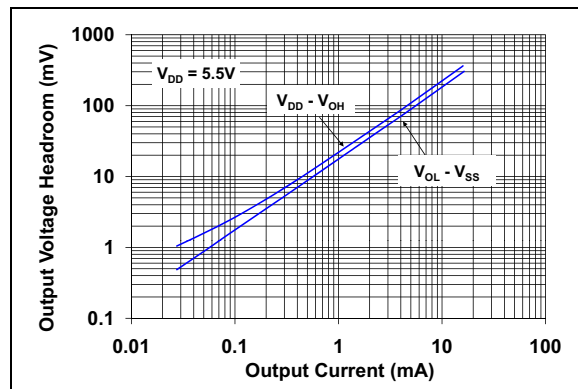
**FIGURE 2-20:** Gain Bandwidth Product, Phase Margin vs. Ambient Temperature.



**FIGURE 2-23:** Output Voltage Headroom vs. Output Current.

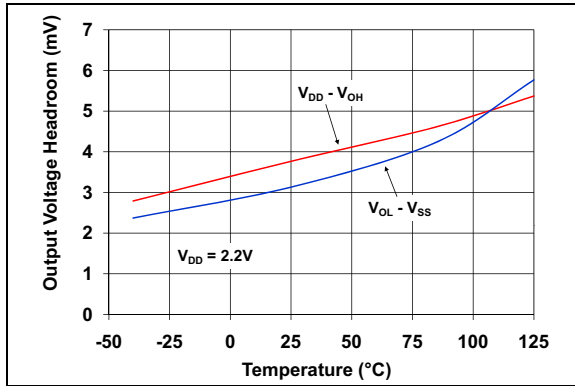


**FIGURE 2-21:** Output Short Circuit Current vs. Power Supply Voltage.

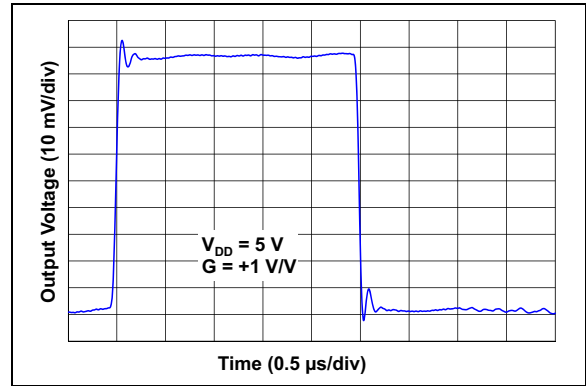


**FIGURE 2-24:** Output Voltage Headroom vs. Output Current.

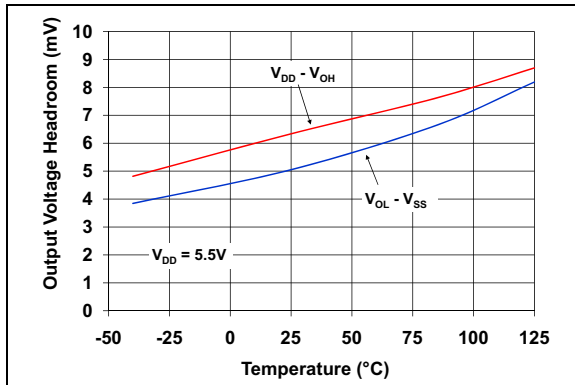
**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = +2.2\text{V}$  to  $+5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 20\text{ pF}$ .



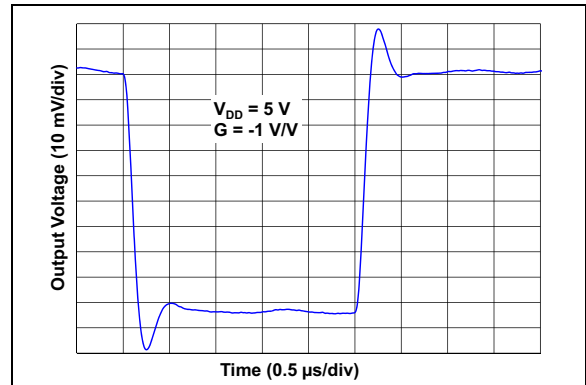
**FIGURE 2-25:** Output Voltage Headroom vs. Ambient Temperature.



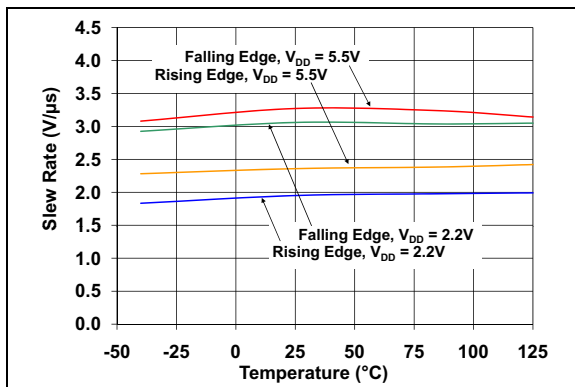
**FIGURE 2-28:** Small Signal Non-Inverting Pulse Response.



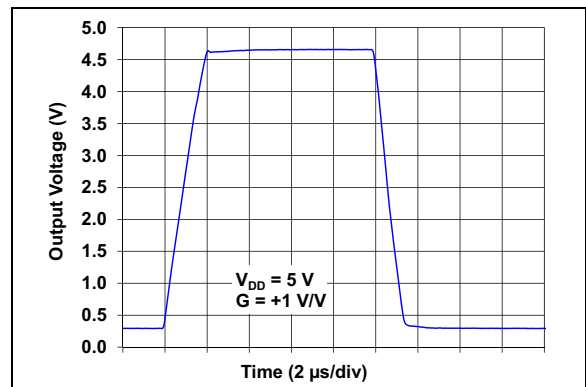
**FIGURE 2-26:** Output Voltage Headroom vs. Ambient Temperature.



**FIGURE 2-29:** Small Signal Inverting Pulse Response.



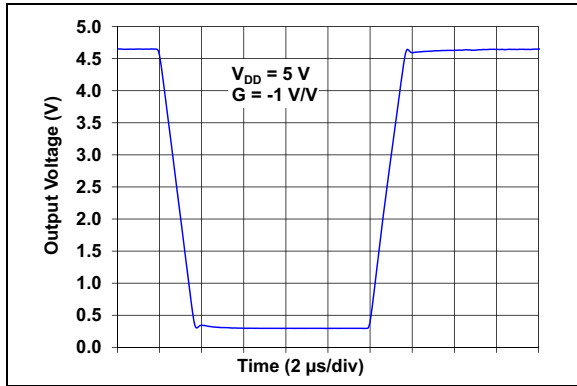
**FIGURE 2-27:** Slew Rate vs. Ambient Temperature.



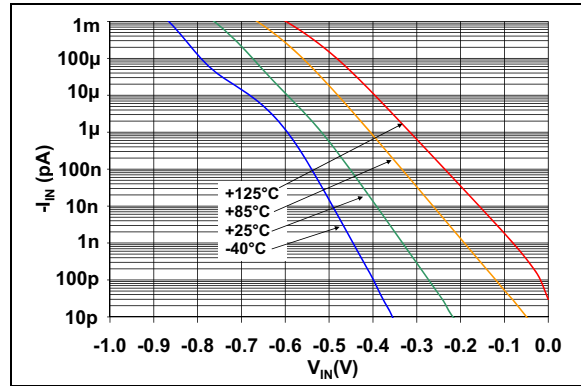
**FIGURE 2-30:** Large Signal Non-Inverting Pulse Response.

# MCP6481/2/4

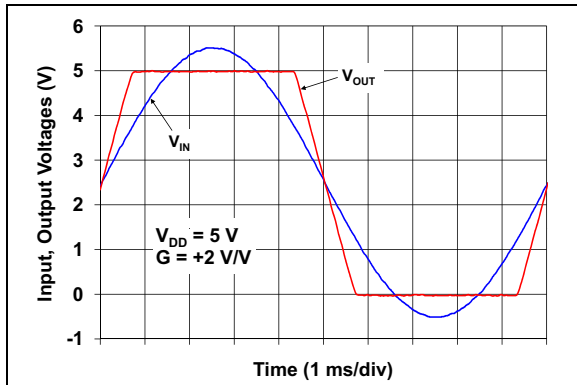
**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = +2.2\text{V}$  to  $+5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{CM} = V_{DD}/2$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 20\text{ pF}$ .



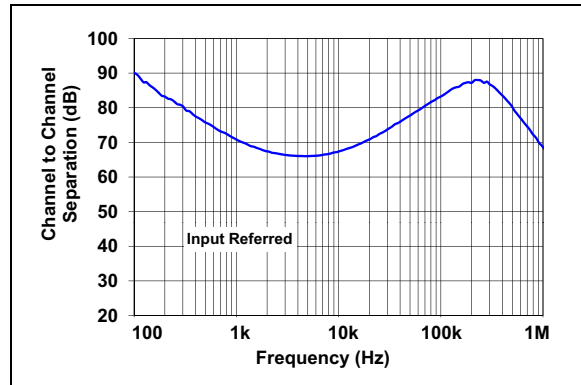
**FIGURE 2-31:** Large Signal Inverting Pulse Response.



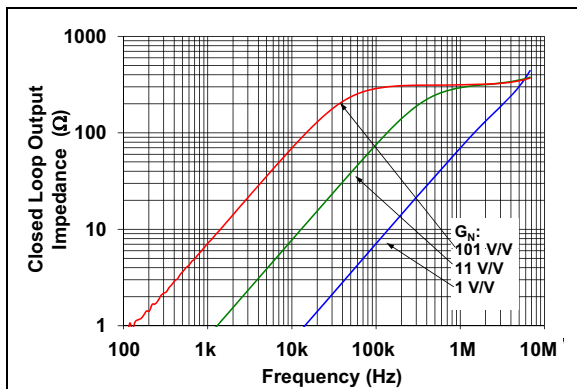
**FIGURE 2-34:** Measured Input Current vs. Input Voltage (below  $V_{SS}$ ).



**FIGURE 2-32:** The MCP6481/2/4 Shows No Phase Reversal.



**FIGURE 2-35:** Channel-to-Channel Separation vs. Frequency (MCP6482/4 only).



**FIGURE 2-33:** Closed Loop Output Impedance vs. Frequency.

## 3.0 PIN DESCRIPTIONS

Descriptions of the pins are listed in [Table 3-1](#).

**TABLE 3-1: PIN FUNCTION TABLE**

MCP6481	MCP6482		MCP6484	Symbol	Description
	SC70, SOT-23	SOIC, MSOP	2x3 TDFN SOIC, TSSOP		
1	1	1	1	$V_{OUT}, V_{OUTA}$	Analog Output (op amp A)
4	2	2	2	$V_{IN-}, V_{INA-}$	Inverting Input (op amp A)
3	3	3	3	$V_{IN+}, V_{INA+}$	Non-inverting Input (op amp A)
5	8	8	4	$V_{DD}$	Positive Power Supply
—	5	5	5	$V_{INB+}$	Non-inverting Input (op amp B)
—	6	6	6	$V_{INB-}$	Inverting Input (op amp B)
—	7	7	7	$V_{OUTB}$	Analog Output (op amp B)
—	—	—	8	$V_{OUTC}$	Analog Output (op amp C)
—	—	—	9	$V_{INC-}$	Inverting Input (op amp C)
—	—	—	10	$V_{INC+}$	Non-Inverting Input (op amp C)
2	4	4	11	$V_{SS}$	Negative Power Supply
—	—	—	12	$V_{IND+}$	Non-Inverting Input (op amp D)
—	—	—	13	$V_{IND-}$	Inverting Input (op amp D)
—	—	—	14	$V_{OUTD}$	Analog Output (op amp D)
—	—	9	—	EP	Exposed Thermal Pad (EP); must be connected to $V_{SS}$ .

### 3.1 Analog Outputs

The output pins are low-impedance voltage sources.

### 3.2 Analog Inputs

The non-inverting and inverting inputs are high-impedance CMOS inputs with low bias currents.

### 3.3 Power Supply Pins

The positive power supply ( $V_{DD}$ ) is 2.2V to 5.5V higher than the negative power supply ( $V_{SS}$ ). For normal operation, the other pins are at voltages between  $V_{SS}$  and  $V_{DD}$ .

Typically, these parts are used in single-supply operation. In this case,  $V_{SS}$  is connected to ground and  $V_{DD}$  is connected to the supply.  $V_{DD}$  will need bypass capacitors.

### 3.4 Exposed Thermal Pad (EP)

There is an internal electrical connection between the Exposed Thermal Pad (EP) and the  $V_{SS}$  pin; they must be connected to the same potential on the Printed Circuit Board (PCB).

This pad can be connected to a PCB ground plane to provide a larger heat sink. This improves the package thermal resistance ( $\theta_{JA}$ ).

# MCP6481/2/4

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NOTES:

## 4.0 APPLICATION INFORMATION

The MCP6481/2/4 family of op amps is manufactured using Microchip's state-of-the-art CMOS process and is specifically designed for low-power, high-precision applications.

### 4.1 Inputs

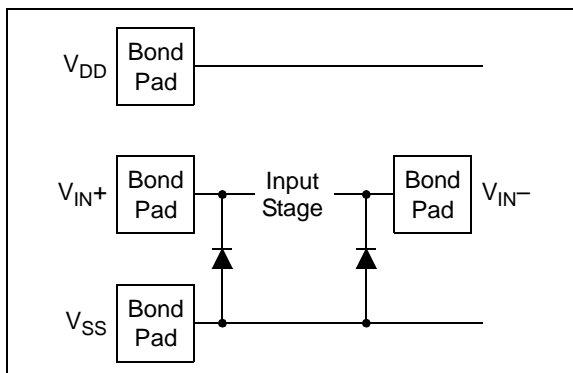
#### 4.1.1 PHASE REVERSAL

The MCP6481/2/4 op amps are designed to prevent phase reversal when the input pins exceed the supply voltages. [Figure 2-32](#) shows the input voltage exceeding the supply voltage without any phase reversal.

#### 4.1.2 INPUT VOLTAGE LIMITS

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the voltages at the input pins (see [Section 1.1 "Absolute Maximum Ratings †"](#)).

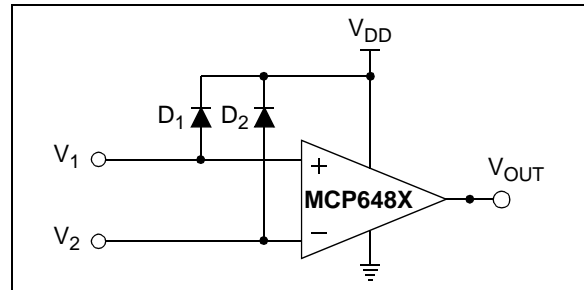
The ESD protection on the inputs can be depicted as shown in [Figure 4-1](#). This structure was chosen to protect the input transistors against many (but not all) overvoltage conditions, and to minimize the input bias current ( $I_B$ ).



**FIGURE 4-1:** Simplified Analog Input ESD Structures.

The input ESD diodes clamp the inputs when they try to go more than one diode drop below  $V_{SS}$ . They also clamp any voltages that go well above  $V_{DD}$ . Their breakdown voltage is high enough to allow normal operation, but not low enough to protect against slow overvoltage (beyond  $V_{DD}$ ) events. Very fast ESD events (that meet the specification) are limited so that damage does not occur.

In some applications, it may be necessary to prevent excessive voltages from reaching the op amp inputs; [Figure 4-2](#) shows one approach to protect these inputs.



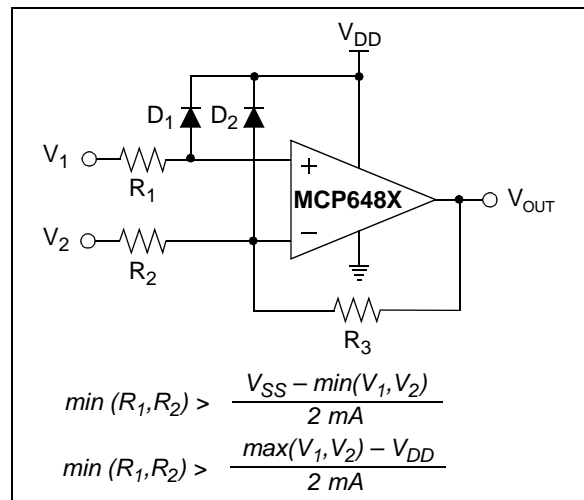
**FIGURE 4-2:** Protecting the Analog Inputs.

A significant amount of current can flow out of the inputs when the Common mode voltage ( $V_{CM}$ ) is below ground ( $V_{SS}$ ), as shown in [Figure 2-34](#).

#### 4.1.3 INPUT CURRENT LIMITS

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the currents into the input pins (see [Section 1.1 "Absolute Maximum Ratings †"](#)).

[Figure 4-3](#) shows one approach to protect these inputs. The  $R_1$  and  $R_2$  resistors limit the possible currents in or out of the input pins (and the ESD diodes,  $D_1$  and  $D_2$ ). The diode currents will go through either  $V_{DD}$  or  $V_{SS}$ .



$$\min(R_1, R_2) > \frac{V_{SS} - \min(V_1, V_2)}{2 \text{ mA}}$$

$$\min(R_1, R_2) > \frac{\max(V_1, V_2) - V_{DD}}{2 \text{ mA}}$$

**FIGURE 4-3:** Protecting the Analog Inputs.

# MCP6481/2/4

## 4.1.4 NORMAL OPERATION

The inputs of the MCP6481/2/4 op amps use two differential input stages in parallel. One operates at a low Common mode input voltage ( $V_{CM}$ ), while the other operates at a high  $V_{CM}$ . With this topology, the device operates with a  $V_{CM}$  up to 0.3V above  $V_{DD}$  and 0.3V below  $V_{SS}$  (refer to Figures 2-3 and 2-4). The input offset voltage is measured at  $V_{CM} = V_{SS} - 0.3V$  and  $V_{DD} + 0.3V$  to ensure proper operation.

The transition between the input stages occurs when  $V_{CM}$  is near  $V_{DD} - 1.2V$  (refer to Figures 2-3 and 2-4). For the best distortion performance and gain linearity, with non-inverting gains, avoid this region of operation.

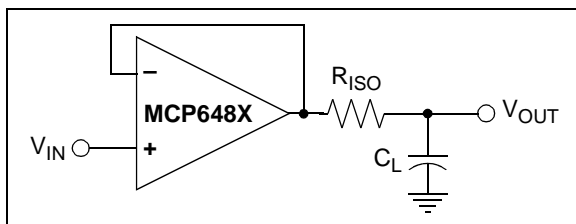
## 4.2 Rail-to-Rail Output

The output voltage range of the MCP6481/2/4 op amps is 0.007V (typical) and 5.493V (typical) when  $R_L = 10\text{ k}\Omega$  is connected to  $V_{DD}/2$  and  $V_{DD} = 5.5V$ . Refer to Figures 2-23 and 2-24 for more information.

## 4.3 Capacitive Loads

Driving large capacitive loads can cause stability problems for voltage feedback op amps. As the load capacitance increases, the feedback loop's phase margin decreases and the closed-loop bandwidth is reduced. This produces gain peaking in the frequency response, with overshoot and ringing in the step response. While a unity-gain buffer ( $G = +1V/V$ ) is the most sensitive to capacitive loads, all gains show the same general behavior.

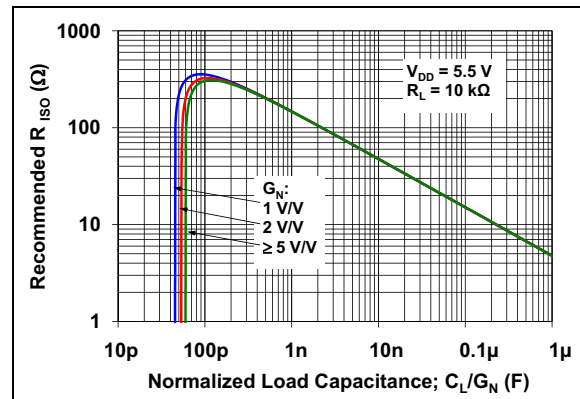
When driving large capacitive loads with these op amps (e.g.,  $> 100\text{ pF}$  when  $G = +1V/V$ ), a small series resistor at the output ( $R_{ISO}$  in Figure 4-4) improves the feedback loop's phase margin (stability) by making the output load resistive at higher frequencies. The bandwidth will generally be lower than the bandwidth with no capacitance load.



**FIGURE 4-4:** Output Resistor,  $R_{ISO}$  Stabilizes Large Capacitive Loads.

Figure 4-5 gives the recommended  $R_{ISO}$  values for different capacitive loads and gains. The x-axis is the normalized load capacitance ( $C_L/G_N$ ), where  $G_N$  is the circuit's noise gain. For non-inverting gains,  $G_N$  and the Signal Gain are equal. For inverting gains,  $G_N$  is  $1 + |\text{Signal Gain}|$  (e.g.,  $-1V/V$  gives  $G_N = +2V/V$ ).

After selecting  $R_{ISO}$  for your circuit, double check the resulting frequency response peaking and step response overshoot. Modify  $R_{ISO}$ 's value until the response is reasonable. Bench evaluation and simulations with the MCP6481/2/4 SPICE macro model are helpful.



**FIGURE 4-5:** Recommended  $R_{ISO}$  Values for Capacitive Loads.

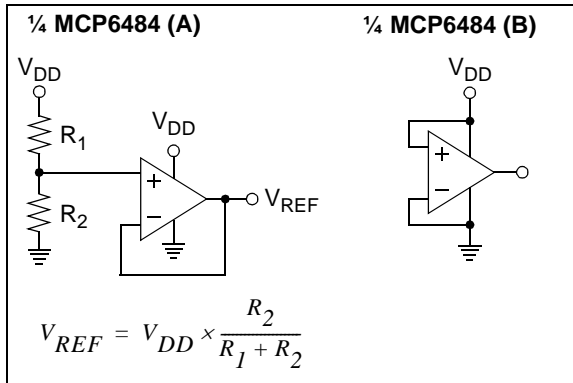
## 4.4 Supply Bypass

With this family of operational amplifiers, the power supply pin ( $V_{DD}$  for single supply) should have a local bypass capacitor (i.e.,  $0.01\text{ }\mu\text{F}$  to  $0.1\text{ }\mu\text{F}$ ) within 2 mm for good high-frequency performance. It can use a bulk capacitor (i.e.,  $1\text{ }\mu\text{F}$  or larger) within 100 mm to provide large, slow currents. This bulk capacitor can be shared with other analog parts.



## 4.5 Unused Op Amps

An unused op amp in a quad package (MCP6484) should be configured as shown in Figure 4-6. These circuits prevent the output from toggling and causing crosstalk. Circuit A sets the op amp at its minimum noise gain. The resistor divider produces any desired reference voltage within the output voltage range of the op amp, and the op amp buffers that reference voltage. Circuit B uses the minimum number of components and operates as a comparator, but it may draw more current.



**FIGURE 4-6:** Unused Op Amps.

## 4.6 PCB Surface Leakage

In applications where low-input bias current is critical, PCB surface leakage effects need to be considered. Surface leakage is caused by humidity, dust or other contamination on the board. Under low-humidity conditions, a typical resistance between nearby traces is  $10^{12}\Omega$ . A 5V difference would cause 5 pA of current to flow, which is greater than the MCP6481/2/4 family's bias current at +25°C (1 pA, typical).

The easiest way to reduce surface leakage is to use a guard ring around sensitive pins (or traces). The guard ring is biased at the same voltage as the sensitive pin. An example of this type of layout is shown in Figure 4-7.



**FIGURE 4-7:** Example Guard Ring Layout for Inverting Gain.

1. Non-Inverting Gain and Unity-Gain Buffer:
  - a. Connect the non-inverting pin ( $V_{IN+}$ ) to the input with a wire that does not touch the PCB surface.
  - b. Connect the guard ring to the inverting input pin ( $V_{IN-}$ ). This biases the guard ring to the Common mode input voltage.
2. Inverting Gain and Transimpedance Gain Amplifiers (convert current to voltage, such as photo detectors):
  - a. Connect the guard ring to the non-inverting input pin ( $V_{IN+}$ ). This biases the guard ring to the same reference voltage as the op amp (e.g.,  $V_{DD}/2$  or ground).
  - b. Connect the inverting pin ( $V_{IN-}$ ) to the input with a wire that does not touch the PCB surface.

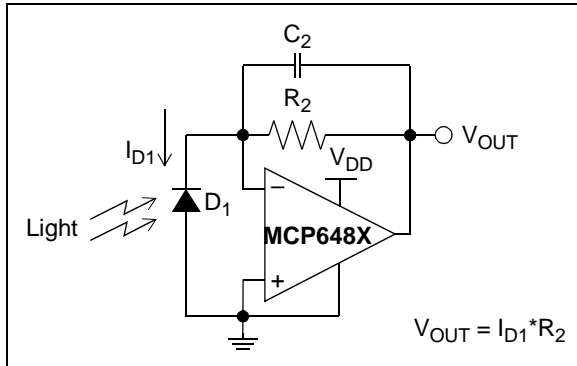
# MCP6481/2/4

## 4.7 Application Circuits

### 4.7.1 PHOTO DETECTION

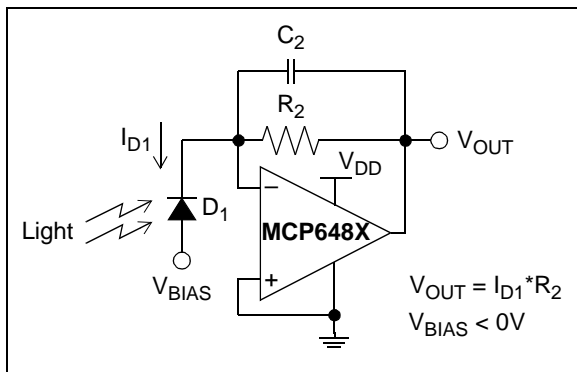
The MCP6481/2/4 op amps can be used to easily convert the signal from a sensor that produces an output current (such as a photo diode) into a voltage (a transimpedance amplifier). This is implemented with a single resistor ( $R_2$ ) in the feedback loop of the amplifiers shown in Figure 4-8 and Figure 4-9. The optional capacitor ( $C_2$ ) sometimes provides stability for these circuits.

A photodiode configured in the Photovoltaic mode has zero voltage potential placed across it (Figure 4-8). In this mode, the light sensitivity and linearity is maximized, making it best suited for precision applications. The key amplifier specifications for this application are: low-input bias current, Common mode input voltage range (including ground), and rail-to-rail output.



**FIGURE 4-8:** Photovoltaic Mode Detector.

In contrast, a photodiode that is configured in the Photoconductive mode has a reverse bias voltage across the photo-sensing element (Figure 4-9). This decreases the diode capacitance, which facilitates high-speed operation (e.g., high-speed digital communications). However, the reverse bias voltage also increased diode leakage current and caused linearity errors.



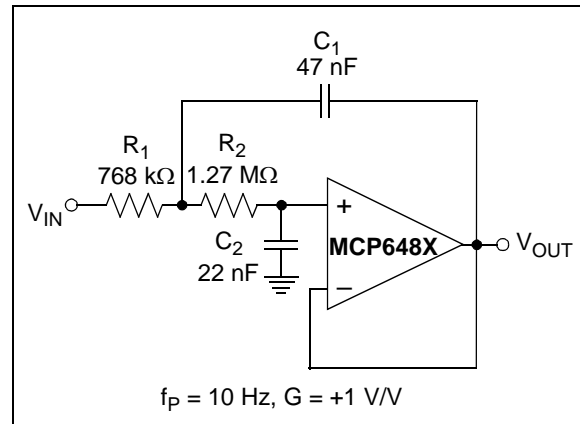
**FIGURE 4-9:** Photoconductive Mode Detector.

### 4.7.2 ACTIVE LOW PASS FILTER

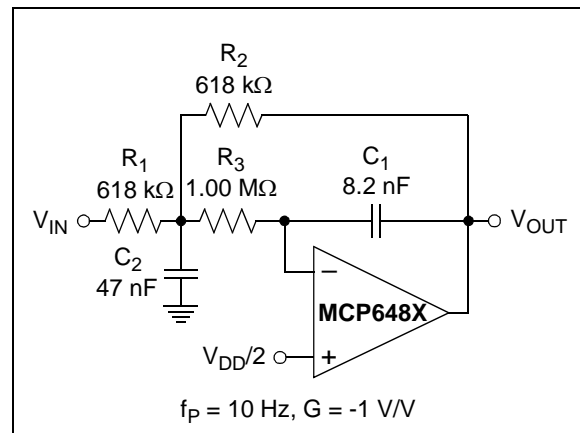
The MCP6481/2/4 op amps' low-input bias current makes it possible for the designer to use larger resistors and smaller capacitors for active low-pass filter applications. However, as the resistance increases, the noise generated also increases. Parasitic capacitances and the large value resistors could also modify the frequency response. These trade-offs need to be considered when selecting circuit elements.

Usually, the op amp bandwidth is 100x the filter cutoff frequency (or higher) for good performance. It is possible to have the op amp bandwidth 10x higher than the cutoff frequency, thus having a design that is more sensitive to component tolerances.

Figure 4-10 and Figure 4-11 show low-pass, second-order, Butterworth filters with a cutoff frequency of 10 Hz. The filter in Figure 4-10 has a non-inverting gain of +1 V/V, and the filter in Figure 4-11 has an inverting gain of -1 V/V.



**FIGURE 4-10:** Second-Order, Low-Pass Butterworth Filter with Sallen-Key Topology.

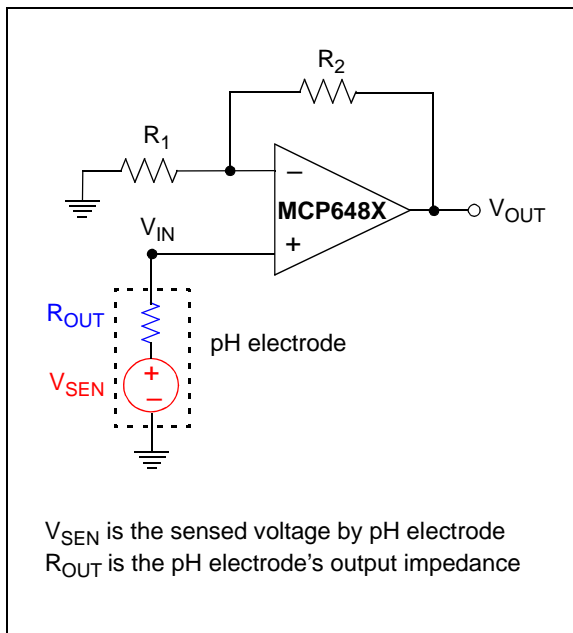


**FIGURE 4-11:** Second-Order, Low-Pass Butterworth Filter with Multiple-Feedback Topology.

### 4.7.3 PH ELECTRODE AMPLIFIER

The MCP6481/2/4 op amps can be used for sensing applications where the sensor has high output impedance, such as a pH electrode sensor; its output impedance is in the range of  $1\text{ M}\Omega$  to  $1\text{ G}\Omega$ . The key op amp specifications for these kinds of applications are low-input bias current and high input impedance.

A typical sensing circuit is shown in [Figure 4-12](#), it is implemented with a non-inverting amplifier which has a gain of  $1+R_2/R_1$ . The input voltage error due to input bias current is equal to  $I_B \cdot R_{OUT}$ , which is amplified by  $1+R_2/R_1$  at the output. To minimize the voltage error and get the  $V_{OUT}$  with better accuracy, the  $I_B$  must be small enough.



**FIGURE 4-12:** pH Electrode Amplifier.

# MCP6481/2/4

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NOTES:

## 5.0 DESIGN AIDS

Microchip Technology Inc. provides the basic design tools needed for the MCP6481/2/4 family of op amps.

### 5.1 SPICE Macro Model

The latest SPICE macro model for the MCP6481/2/4 op amps is available on the Microchip web site at [www.microchip.com](http://www.microchip.com). The model was written and tested in PSpice, owned by Orcad (Cadence®). For other simulators, translation may be required.

The model covers a wide aspect of the op amp's electrical specifications. Not only does the model cover voltage, current and resistance of the op amp, but it also covers the temperature and noise effects on the behavior of the op amp. The model has not been verified outside the specification range listed in the op amp data sheet. The model behaviors under these conditions cannot be guaranteed to match the actual op amp performance.

Moreover, the model is intended to be an initial design tool. Bench testing is a very important part of any design and cannot be replaced with simulations. Also, simulation results using this macro model need to be validated by comparing them to the data sheet specifications and characteristic curves.

### 5.2 FilterLab Software

Microchip's FilterLab software is an innovative software tool that simplifies analog active filter (using op amps) design. Available at no cost from the Microchip web site at [www.microchip.com/filterlab](http://www.microchip.com/filterlab), the FilterLab design tool provides full schematic diagrams of the filter circuit with component values. It also outputs the filter circuit in SPICE format, which can be used with the macro model to simulate actual filter performance.

### 5.3 MAPS (Microchip Advanced Part Selector)

MAPS is a software tool that helps semiconductor professionals efficiently identify Microchip devices that fit a particular design requirement. Available at no cost, MAPS is an overall selection tool for Microchip's product portfolio that includes analog, memory, MCUs and DSCs. Using this tool, you can define a filter to sort features for a parametric search of devices and export side-by-side technical comparison reports. Helpful links are also provided for data sheets, purchases and sampling of Microchip parts. The web site is available at [www.microchip.com/maps](http://www.microchip.com/maps).

## 5.4 Analog Demonstration and Evaluation Boards

Microchip offers a broad spectrum of Analog Demonstration and Evaluation Boards that are designed to help you achieve faster time to market. For a complete listing of these boards and their corresponding user's guides and technical information, visit the Microchip web site:

[www.microchip.com/analogtools](http://www.microchip.com/analogtools).

Some boards that are especially useful include:

- MCP6XXX Amplifier Evaluation Board 1
- MCP6XXX Amplifier Evaluation Board 2
- MCP6XXX Amplifier Evaluation Board 3
- MCP6XXX Amplifier Evaluation Board 4
- Active Filter Demo Board Kit
- 5/6-Pin SOT-23 Evaluation Board, part number VSUPEV2
- 8-Pin SOIC/MSOP/TSSOP/DIP Evaluation Board, part number SOIC8EV

## 5.5 Application Notes

The following Microchip analog design note and application notes are available on the Microchip web site at [www.microchip.com/appnotes](http://www.microchip.com/appnotes), and are recommended as supplemental reference resources.

- **ADN003:** "Select the Right Operational Amplifier for your Filtering Circuits", DS21821
- **AN722:** "Operational Amplifier Topologies and DC Specifications", DS00722
- **AN723:** "Operational Amplifier AC Specifications and Applications", DS00723
- **AN884:** "Driving Capacitive Loads With Op Amps", DS00884
- **AN990:** "Analog Sensor Conditioning Circuits – An Overview", DS00990
- **AN1177:** "Op Amp Precision Design: DC Errors", DS01177
- **AN1228:** "Op Amp Precision Design: Random Noise", DS01228
- **AN1297:** "Microchip's Op Amp SPICE Macro Models" DS01297
- **AN1332:** "Current Sensing Circuit Concepts and Fundamentals" DS01332
- **AN1494:** "Using MCP6491 Op Amps for Photodetection Applications" DS01494

These application notes and others are listed in:

- "Signal Chain Design Guide", DS21825

# MCP6481/2/4

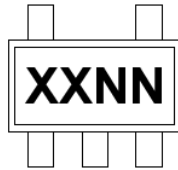
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NOTES:

## 6.0 PACKAGING INFORMATION

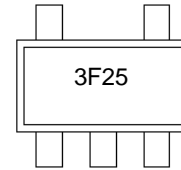
### 6.1 Package Marking Information

#### 5-Lead SOT-23 (MCP6481 only)

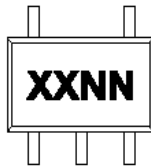


Part Number	Code
MCP6481T-E/OT	3FNN

#### Example

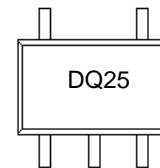


#### 5-Lead SC-70 (MCP6481 only)

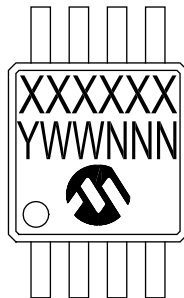


Part Number	Code
MCP6481T-E/LTY	DQNN

#### Example



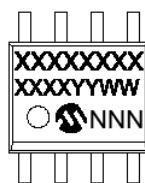
#### 8-Lead MSOP (3x3 mm) (MCP6482 only)



#### Example



#### 8-Lead SOIC (3.90 mm) (MCP6482 only)



#### Example



<b>Legend:</b>	XX...X	Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.

**Note:** In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

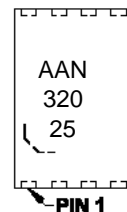
# MCP6481/2/4

8-Lead TDFN (2x3x0.75 mm) (**MCP6482 only**)

Example

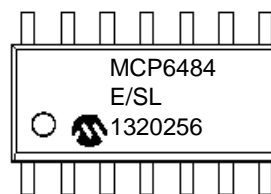
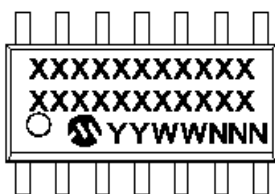


Part Number	Code
MCP6482T-E/MNY	AAN



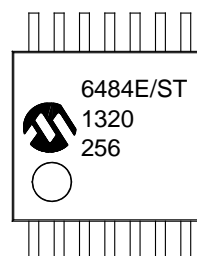
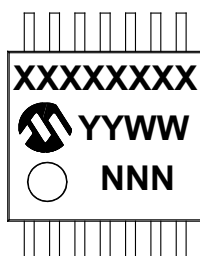
14-Lead SOIC (3.90 mm) (**MCP6484 only**)

Example



14-Lead TSSOP (4.4 mm) (**MCP6484 only**)

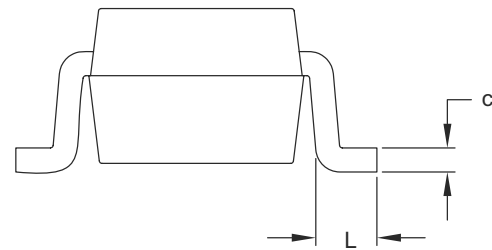
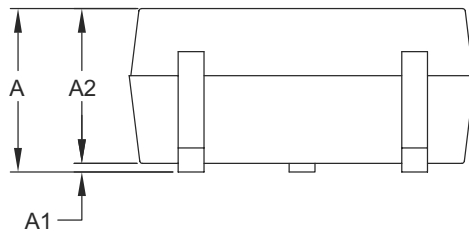
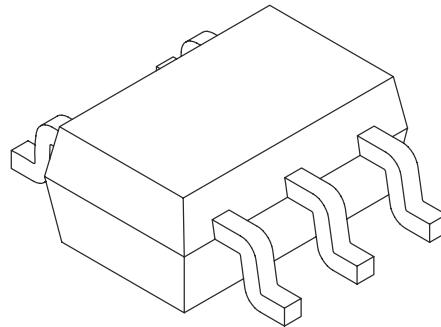
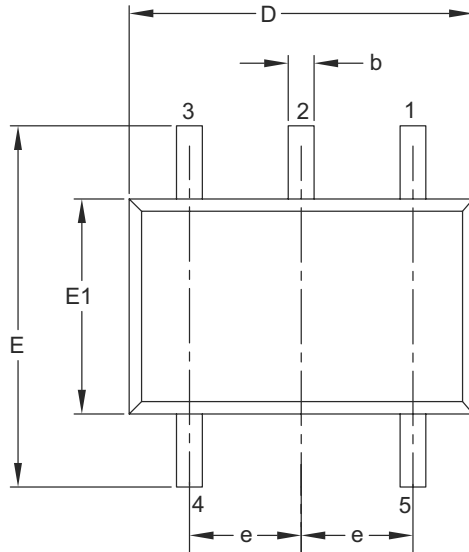
Example





## 5-Lead Plastic Small Outline Transistor (LTY) [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Pins	N	5		
Pitch	e	0.65 BSC		
Overall Height	A	0.80	–	1.10
Molded Package Thickness	A2	0.80	–	1.00
Standoff	A1	0.00	–	0.10
Overall Width	E	1.80	2.10	2.40
Molded Package Width	E1	1.15	1.25	1.35
Overall Length	D	1.80	2.00	2.25
Foot Length	L	0.10	0.20	0.46
Lead Thickness	c	0.08	–	0.26
Lead Width	b	0.15	–	0.40

**Notes:**

- Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- Dimensioning and tolerancing per ASME Y14.5M.

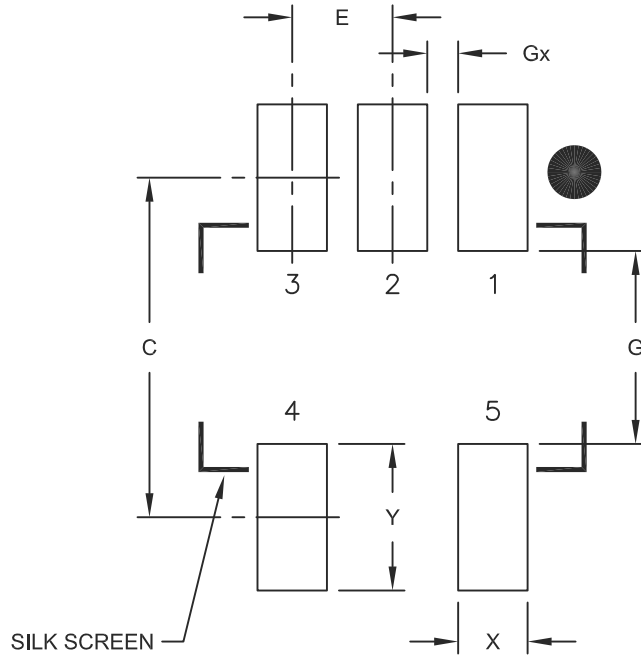
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-061B

# MCP6481/2/4

## 5-Lead Plastic Small Outline Transistor (LTY) [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



RECOMMENDED LAND PATTERN

Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Contact Pitch	E	0.65 BSC		
Contact Pad Spacing	C		2.20	
Contact Pad Width	X			0.45
Contact Pad Length	Y			0.95
Distance Between Pads	G	1.25		
Distance Between Pads	Gx	0.20		

**Notes:**

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2061A

## 5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Pins	N	5		
Lead Pitch	e	0.95 BSC		
Outside Lead Pitch	e1	1.90 BSC		
Overall Height	A	0.90	–	1.45
Molded Package Thickness	A2	0.89	–	1.30
Standoff	A1	0.00	–	0.15
Overall Width	E	2.20	–	3.20
Molded Package Width	E1	1.30	–	1.80
Overall Length	D	2.70	–	3.10
Foot Length	L	0.10	–	0.60
Footprint	L1	0.35	–	0.80
Foot Angle	$\phi$	0°	–	30°
Lead Thickness	c	0.08	–	0.26
Lead Width	b	0.20	–	0.51

**Notes:**

- Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- Dimensioning and tolerancing per ASME Y14.5M.

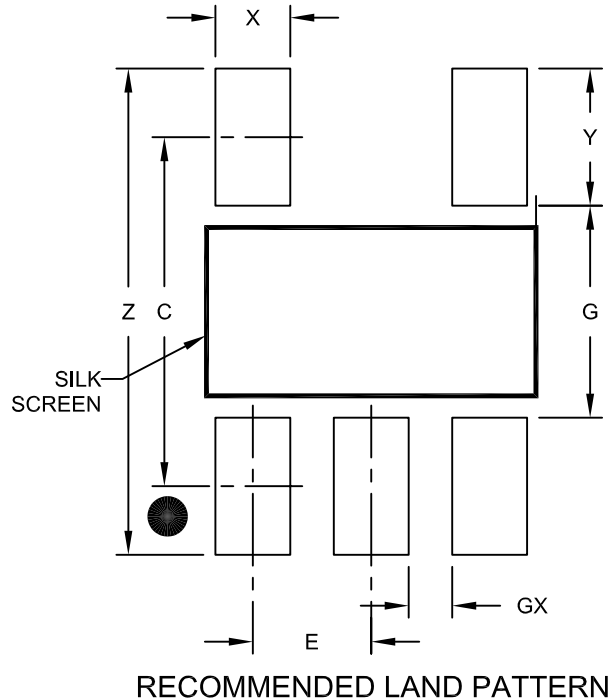
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-091B

# MCP6481/2/4

## 5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Contact Pitch	E	0.95 BSC		
Contact Pad Spacing	C		2.80	
Contact Pad Width (X5)	X			0.60
Contact Pad Length (X5)	Y			1.10
Distance Between Pads	G	1.70		
Distance Between Pads	GX	0.35		
Overall Width	Z			3.90

**Notes:**

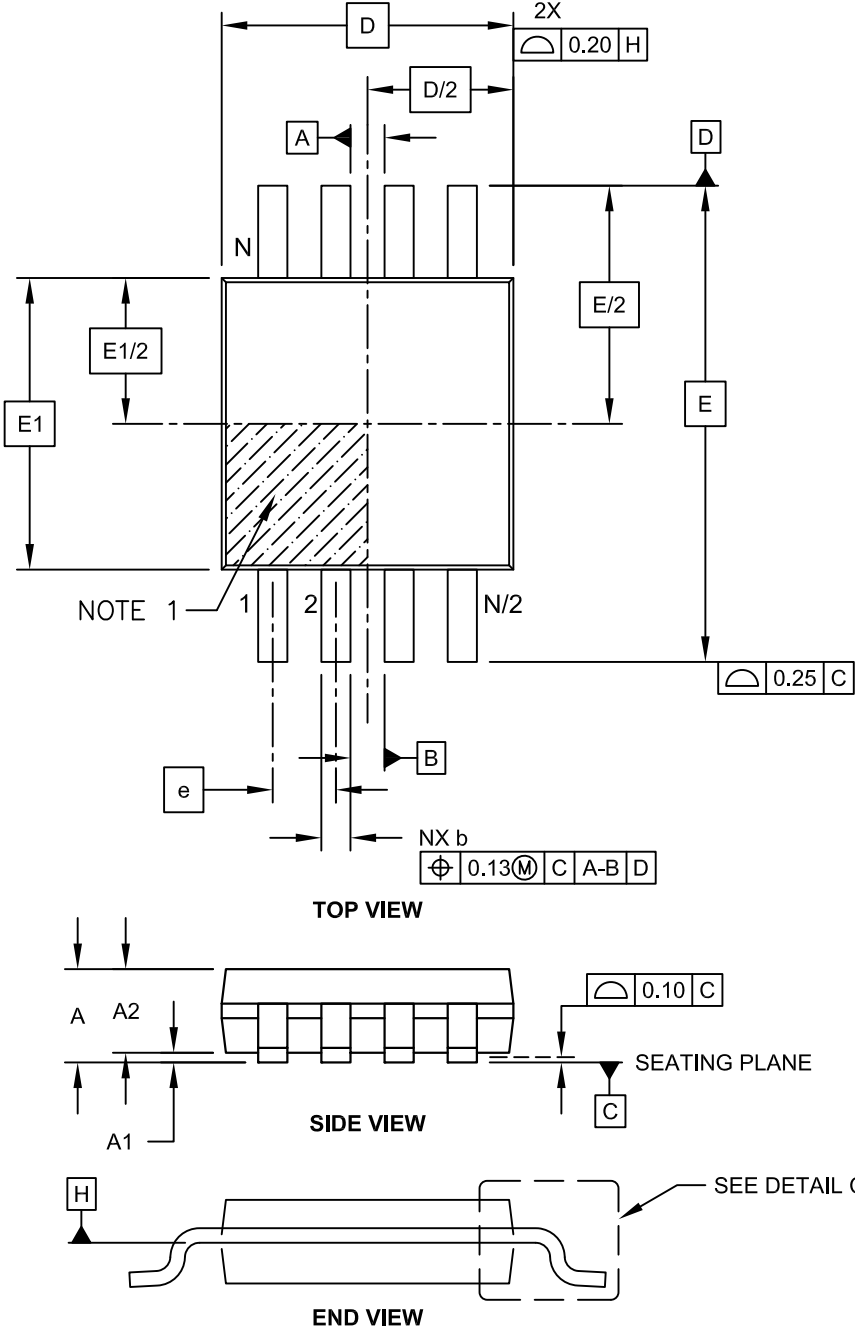
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2091A

## 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>

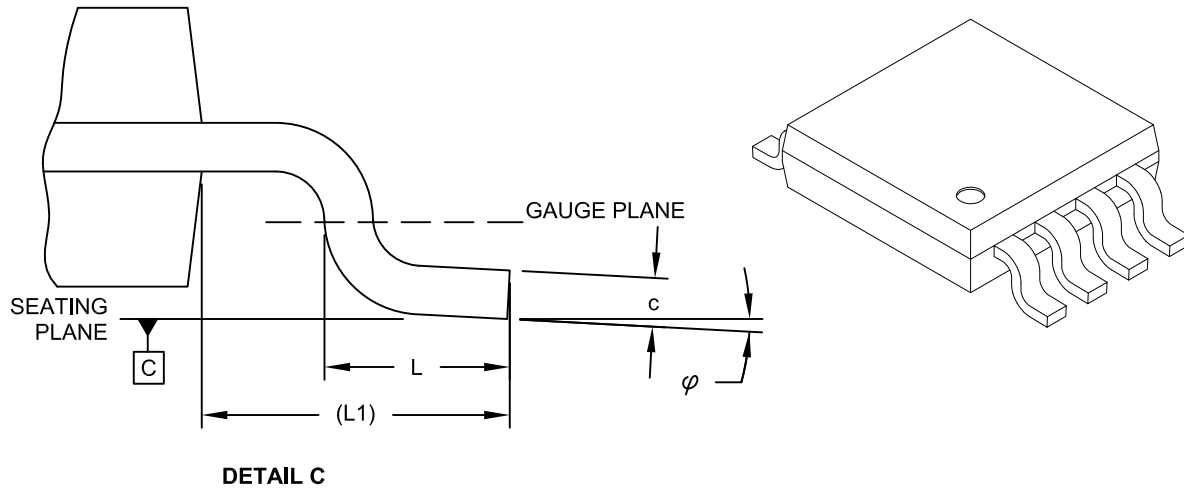


Microchip Technology Drawing C04-111C Sheet 1 of 2

# MCP6481/2/4

## 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	e	0.65 BSC		
Overall Height	A	-	-	1.10
Molded Package Thickness	A2	0.75	0.85	0.95
Standoff	A1	0.00	-	0.15
Overall Width	E	4.90 BSC		
Molded Package Width	E1	3.00 BSC		
Overall Length	D	3.00 BSC		
Foot Length	L	0.40	0.60	0.80
Footprint	L1	0.95 REF		
Foot Angle	$\phi$	0°	-	8°
Lead Thickness	c	0.08	-	0.23
Lead Width	b	0.22	-	0.40

**Notes:**

- Pin 1 visual index feature may vary, but must be located within the hatched area.
- Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-111C Sheet 2 of 2

## 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



RECOMMENDED LAND PATTERN

Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Contact Pitch	E	0.65 BSC		
Contact Pad Spacing	C		4.40	
Overall Width	Z			5.85
Contact Pad Width (X8)	X1			0.45
Contact Pad Length (X8)	Y1			1.45
Distance Between Pads	G1	2.95		
Distance Between Pads	GX	0.20		

**Notes:**

1. Dimensioning and tolerancing per ASME Y14.5M

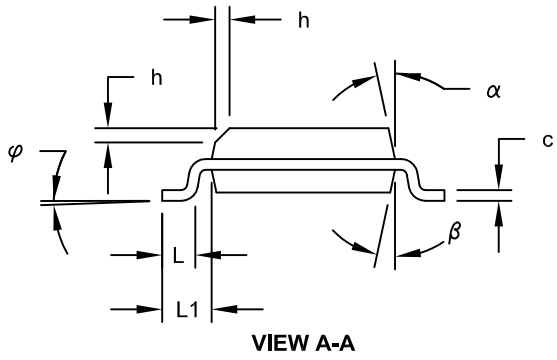
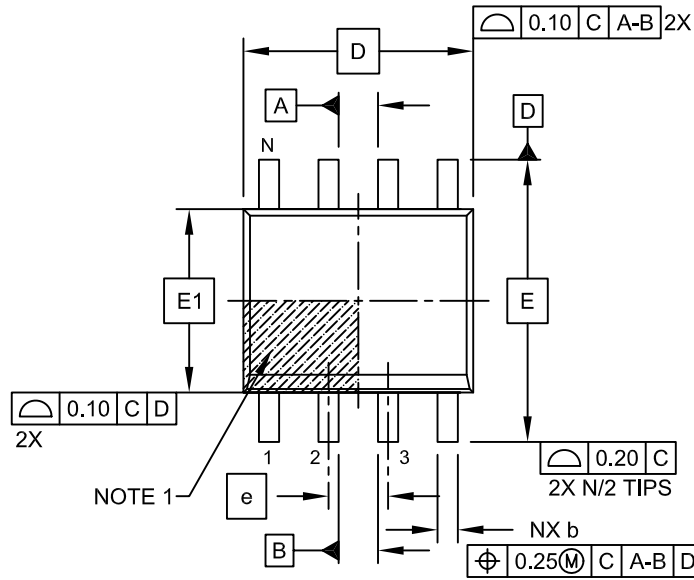
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2111A

# MCP6481/2/4

## 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Microchip Technology Drawing No. C04-057C Sheet 1 of 2



## 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Pins	N	8		
Pitch	e	1.27 BSC		
Overall Height	A	-	-	1.75
Molded Package Thickness	A2	1.25	-	-
Standoff §	A1	0.10	-	0.25
Overall Width	E	6.00 BSC		
Molded Package Width	E1	3.90 BSC		
Overall Length	D	4.90 BSC		
Chamfer (Optional)	h	0.25	-	0.50
Foot Length	L	0.40	-	1.27
Footprint	L1	1.04 REF		
Foot Angle	$\varphi$	0°	-	8°
Lead Thickness	c	0.17	-	0.25
Lead Width	b	0.31	-	0.51
Mold Draft Angle Top	$\alpha$	5°	-	15°
Mold Draft Angle Bottom	$\beta$	5°	-	15°

**Notes:**

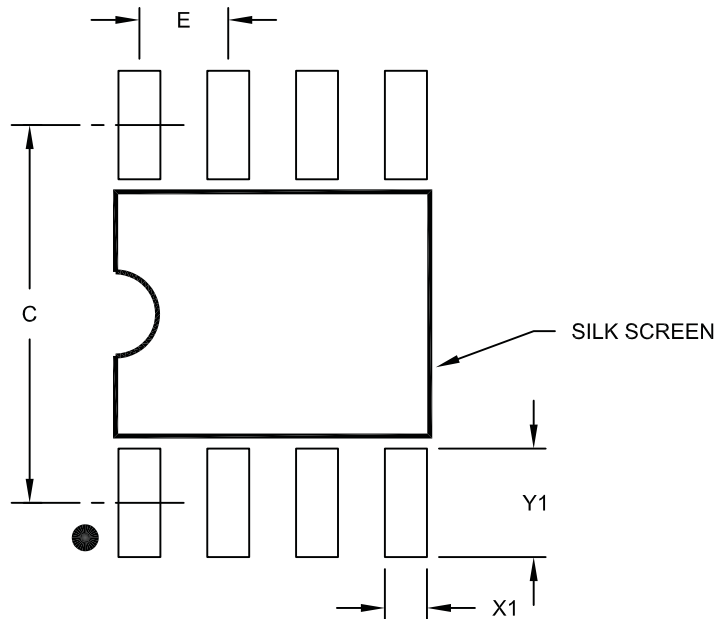
- Pin 1 visual index feature may vary, but must be located within the hatched area.
- § Significant Characteristic
- Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- Dimensioning and tolerancing per ASME Y14.5M
  - BSC: Basic Dimension. Theoretically exact value shown without tolerances.
  - REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

# MCP6481/2/4

## 8-Lead Plastic Small Outline (SN) – Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



RECOMMENDED LAND PATTERN

		Units	MILLIMETERS		
Dimension Limits			MIN	NOM	MAX
Contact Pitch	E		1.27 BSC		
Contact Pad Spacing	C			5.40	
Contact Pad Width (X8)	X1				0.60
Contact Pad Length (X8)	Y1				1.55

Notes:

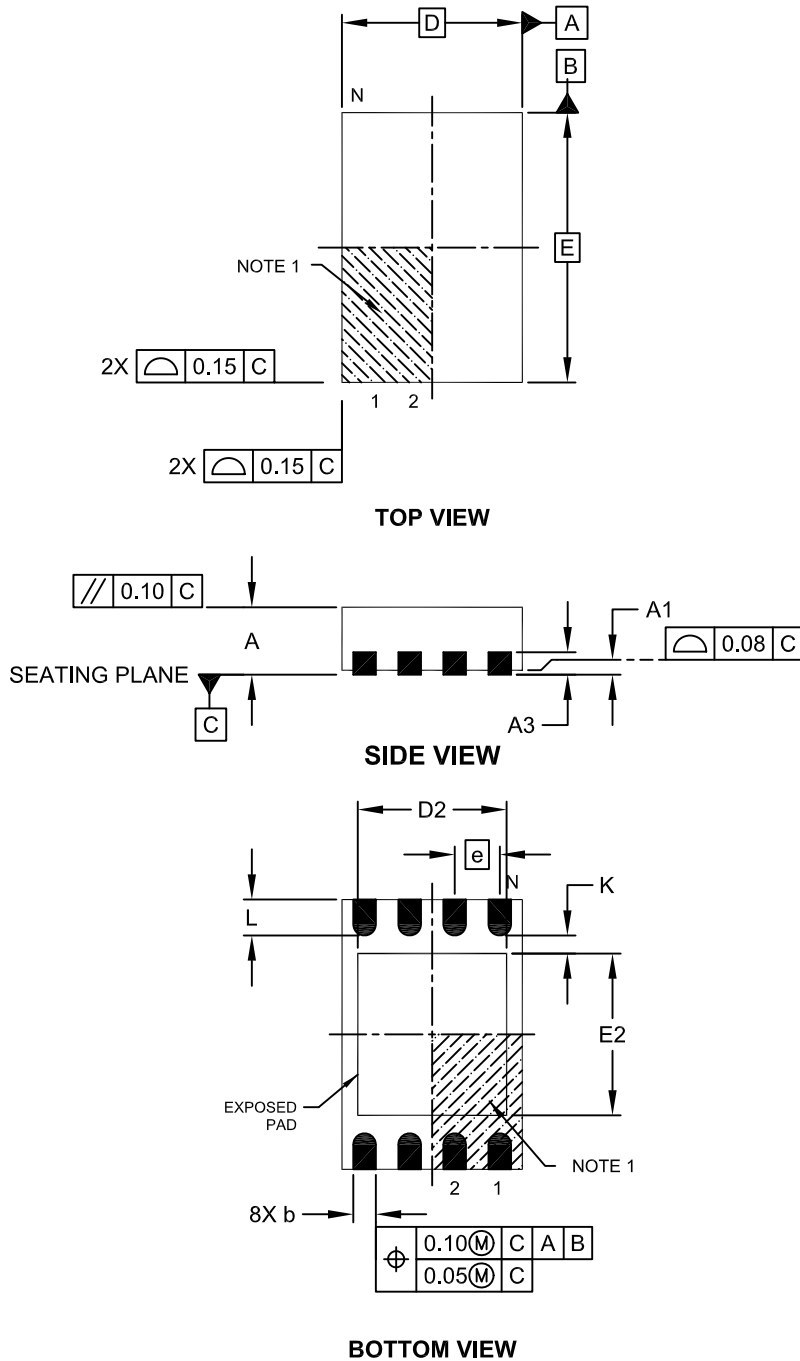
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2057A

## 8-Lead Plastic Dual Flat, No Lead Package (MN) – 2x3x0.75mm Body [TDFN]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Microchip Technology Drawing No. C04-129C Sheet 1 of 2

# MCP6481/2/4

## 8-Lead Plastic Dual Flat, No Lead Package (MN) – 2x3x0.75mm Body [TDFN]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



		Units	MILLIMETERS		
Dimension Limits			MIN	NOM	MAX
Number of Pins	N		8		
Pitch	e		0.50 BSC		
Overall Height	A		0.70	0.75	0.80
Standoff	A1		0.00	0.02	0.05
Contact Thickness	A3		0.20 REF		
Overall Length	D		2.00 BSC		
Overall Width	E		3.00 BSC		
Exposed Pad Length	D2		1.20	-	1.60
Exposed Pad Width	E2		1.20	-	1.60
Contact Width	b		0.20	0.25	0.30
Contact Length	L		0.25	0.30	0.45
Contact-to-Exposed Pad	K		0.20	-	-

### Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. Package may have one or more exposed tie bars at ends.
3. Package is saw singulated
4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-129C Sheet 2 of 2

## 8-Lead Plastic Dual Flat, No Lead Package (MN) – 2x3x0.75 mm Body [TDFN]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Contact Pitch	E	0.50 BSC		
Optional Center Pad Width	W2			1.46
Optional Center Pad Length	T2			1.36
Contact Pad Spacing	C1	3.00		
Contact Pad Width (X8)	X1			0.30
Contact Pad Length (X8)	Y1			0.75
Distance Between Pads	G	0.20		

**Notes:**

1. Dimensioning and tolerancing per ASME Y14.5M

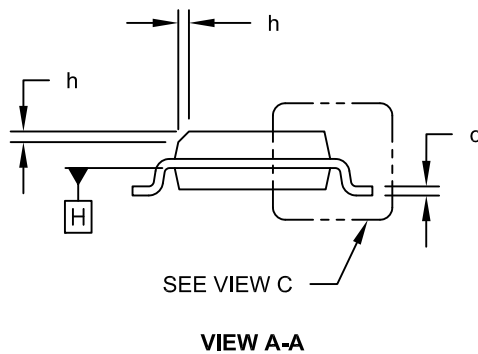
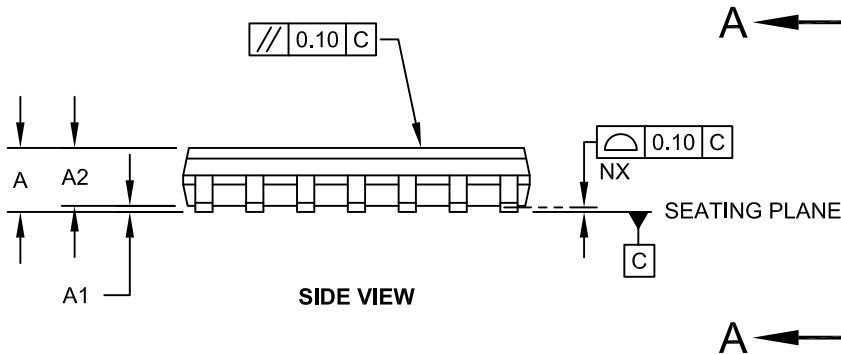
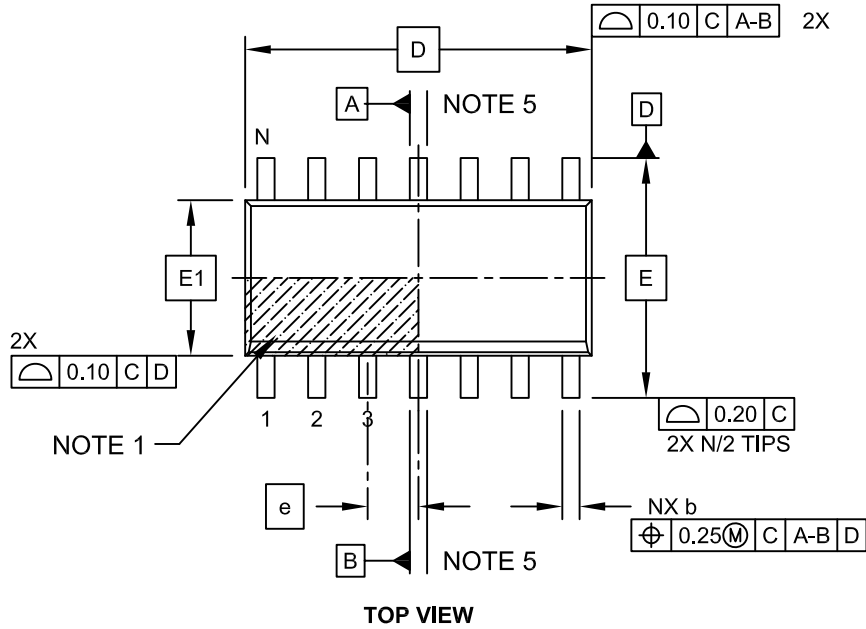
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2129A

# MCP6481/2/4

## 14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

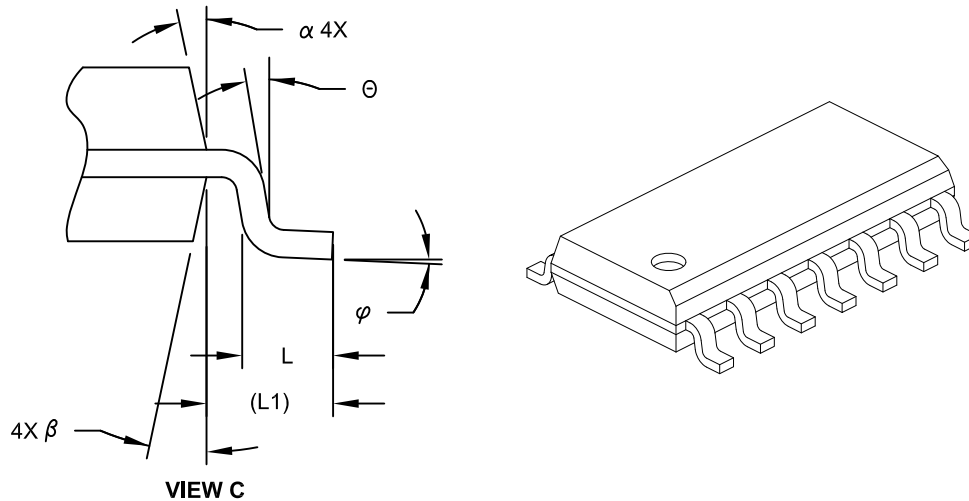
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Microchip Technology Drawing No. C04-065C Sheet 1 of 2

## 14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Pins	N	14		
Pitch	e	1.27 BSC		
Overall Height	A	-	-	1.75
Molded Package Thickness	A2	1.25	-	-
Standoff §	A1	0.10	-	0.25
Overall Width	E	6.00 BSC		
Molded Package Width	E1	3.90 BSC		
Overall Length	D	8.65 BSC		
Chamfer (Optional)	h	0.25	-	0.50
Foot Length	L	0.40	-	1.27
Footprint	L1	1.04 REF		
Lead Angle	$\Theta$	0°	-	-
Foot Angle	$\varphi$	0°	-	8°
Lead Thickness	c	0.10	-	0.25
Lead Width	b	0.31	-	0.51
Mold Draft Angle Top	$\alpha$	5°	-	15°
Mold Draft Angle Bottom	$\beta$	5°	-	15°

**Notes:**

- Pin 1 visual index feature may vary, but must be located within the hatched area.
- § Significant Characteristic
- Dimension D does not include mold flash, protrusions or gate burrs, which shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion, which shall not exceed 0.25 mm per side.
- Dimensioning and tolerancing per ASME Y14.5M  
BSC: Basic Dimension. Theoretically exact value shown without tolerances.  
REF: Reference Dimension, usually without tolerance, for information purposes only.
- Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-065C Sheet 2 of 2

# MCP6481/2/4

14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



RECOMMENDED LAND PATTERN

Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Contact Pitch	E	1.27 BSC		
Contact Pad Spacing	C		5.40	
Contact Pad Width	X			0.60
Contact Pad Length	Y			1.50
Distance Between Pads	Gx	0.67		
Distance Between Pads	G	3.90		

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

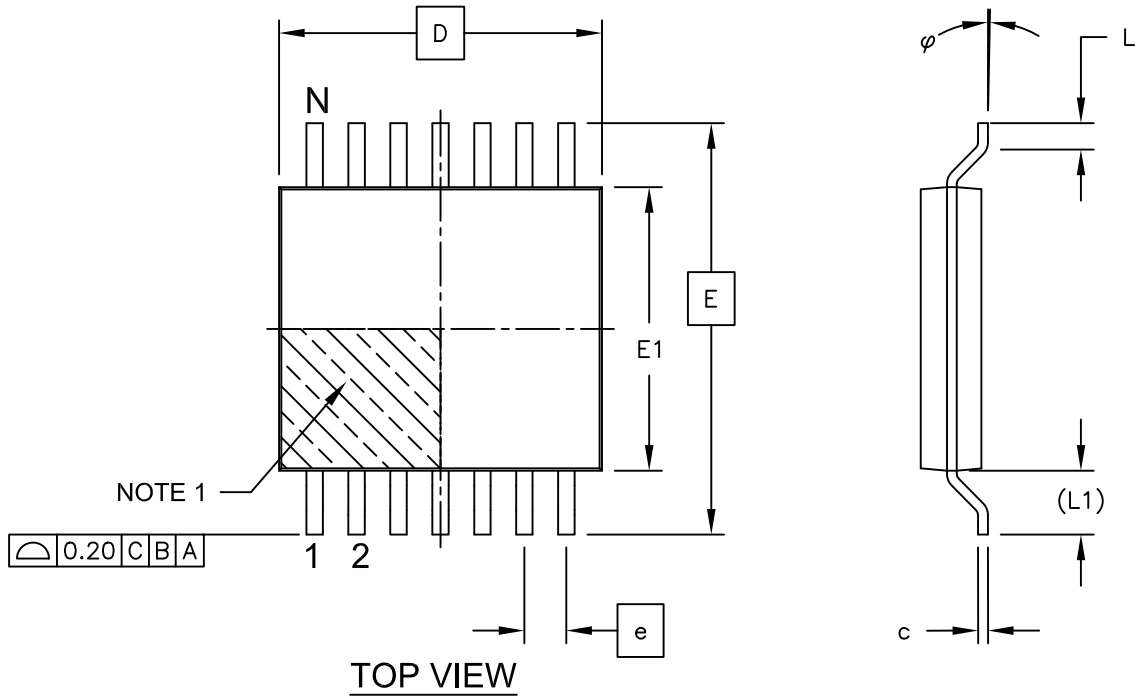
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2065A



## 14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Microchip Technology Drawing C04-087C Sheet 1 of 2

# MCP6481/2/4

## 14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Pins	N	14		
Pitch	e	0.65 BSC		
Overall Height	A	-	-	1.20
Molded Package Thickness	A2	0.80	1.00	1.05
Standoff	A1	0.05	-	0.15
Overall Width	E	6.40 BSC		
Molded Package Width	E1	4.30	4.40	4.50
Molded Package Length	D	4.90	5.00	5.10
Foot Length	L	0.45	0.60	0.75
Footprint	(L1)	1.00 REF		
Foot Angle	$\varphi$	0°	-	8°
Lead Thickness	c	0.09	-	0.20
Lead Width	b	0.19	-	0.30

**Notes:**

1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
3. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-087C Sheet 2 of 2

## 14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



RECOMMENDED LAND PATTERN

		Units	MILLIMETERS		
Dimension Limits			MIN	NOM	MAX
Contact Pitch	E		0.65 BSC		
Contact Pad Spacing	C1			5.90	
Contact Pad Width (X14)	X1				0.45
Contact Pad Length (X14)	Y1				1.45
Distance Between Pads	G	0.20			

**Notes:**

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2087A

# MCP6481/2/4

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NOTES:

## APPENDIX A: REVISION HISTORY

### Revision C (June 2013)

The following is the list of modifications:

1. Added new devices to the family (MCP6482 and MCP6484) and related information throughout the document.
2. Updated thermal package resistance information in [Table 1-3](#).
3. Added [Figure 2-35](#) in [Section 2.0, Typical Performance Curves](#).
4. Updated [Section 3.0, Pin Descriptions](#).
5. Added new [Section 4.5, Unused Op Amps](#).
6. Updated the list of reference documents in [Section 5.5, Application Notes](#).
7. Added package markings and drawings for the MCP6482 and MCP6484 devices.
8. Updated [Product Identification System](#).

### Revision B (October 2012)

The following is the list of modifications:

1. Updated the maximum low input offset voltage value in the [Section "Features"](#).
2. Updated the minimum and maximum input offset voltage in [Table 1-1 "DC Electrical Specifications"](#).
3. Replaced [FIGURE 2-1: "Input Offset Voltage."](#)

### Revision A (September 2012)

- Original Release of this Document.

# MCP6481/2/4

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NOTES:

## PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

<u>PART NO.</u>	<u>-X</u>	<u>/XX</u>	<b>Examples:</b>
Device	Temperature Range	Package	
<b>Device:</b>	MCP6481T:	Single Op Amp (Tape and Reel) (SC70, SOT-23)	a) MCP6481T-E/LTY: Tape and Reel, Extended Temp., 5LD SC70 package
	MCP6482:	Dual Op Amp (SOIC and MSOP only)	b) MCP6481T-E/OT: Tape and Reel, Extended Temp., 5LD SOT-23 package
	MCP6482T:	Dual Op Amp (Tape and Reel) (SOIC, MSOP and 2x3 TDFN)	c) MCP6482-E/MS: Extended Temp., 8LD MSOP package
	MCP6484:	Quad Op Amp	d) MCP6482T-E/MS: Tape and Reel, Extended Temp., 8LD MSOP package
	MCP6484T:	Quad Op Amp (Tape and Reel) (SOIC and TSSOP)	e) MCP6482-E/SN: Extended Temp., 8LD SOIC package
<b>Temperature Range:</b>	E	= -40°C to +125°C (Extended)	f) MCP6482T-E/SN: Tape and Reel, Extended Temp., 8LD SOIC package
<b>Package:</b>	LTY	= Plastic Package (SC70), 5-lead	g) MCP6482T-E/MNY: Tape and Reel, Extended Temp., 8LD 2x3 TDFN package
	OT	= Plastic Small Outline Transistor, (SOT-23), 5-lead	h) MCP6484-E/SL: Extended Temp., 14LD SOIC package
	MNY*	= Plastic Dual Flat, No Lead, (2x3 TDFN), 8-lead (TDFN)	i) MCP6484T-E/SL: Tape and Reel, Extended Temp., 14LD SOIC package
	SN	= Lead Plastic Small Outline (150 mil body), 8-lead (SOIC)	j) MCP6484-E/ST: Extended Temp., 14LD TSSOP package
	MS	= Plastic MSOP, 8-lead	k) MCP6484T-E/ST: Tape and Reel, Extended Temp., 14LD TSSOP package
	SL	= Plastic Small Outline, (150 mil body), 14-lead (SOIC)	
	ST	= Plastic Thin Shrink Small Outline (150 mil body), 14-lead (TSSOP)	
	* Y = Nickel palladium gold manufacturing designator. Only available on the TDFN package.		

# MCP6481/2/4

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NOTES:



**Note the following details of the code protection feature on Microchip devices:**

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as “unbreakable.”

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*Microchip received ISO/TS-16949:2009 certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona; Gresham, Oregon and design centers in California and India. The Company's quality system processes and procedures are for its PIC<sup>®</sup> MCUs and dsPIC<sup>®</sup> DSCs, KEELOQ<sup>®</sup> code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.*

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